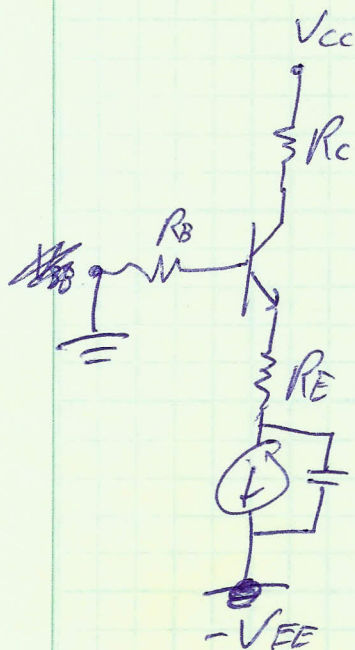


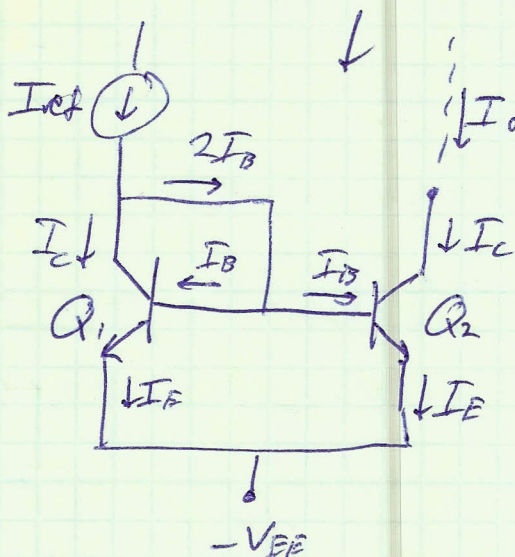
Current Mirrors

- Purpose of stable bias circuit is I_C or I_D independent of transistor parameters and temperature variation
- Can also use current bias



Note that capacitor is needed for signal to pass
 Otherwise current would be constant, including AC part
 Only necessary for ideal current sources
 Not needed with the designs we will use

Identical Transistors



- Q_1 is ON because of I_{ref}
- $V_{CE1} = V_{BE1} = V_{D0} \rightarrow$ active
- $V_{BE2} = V_{BE1} \rightarrow I_{C2} = I_{C1}$
- If Q_2 also in active state:

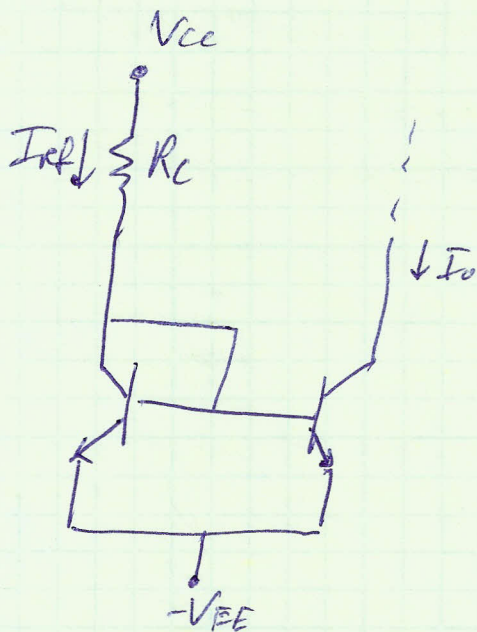
$$I_B = \frac{I_C}{\beta}, \quad I_O = I_C = \beta I_B$$

$$I_{ref} = I_C + 2I_B = (\beta + 2)I_B$$

$$\frac{I_O}{I_{ref}} = \frac{\beta}{\beta + 2} = \frac{1}{1 + 2/\beta} \approx 1$$

- $I_O = I_{ref}$, no matter what is attached to Q_2
- For Q_2 in active state, V_{CE2} must be $\geq V_{D0}$

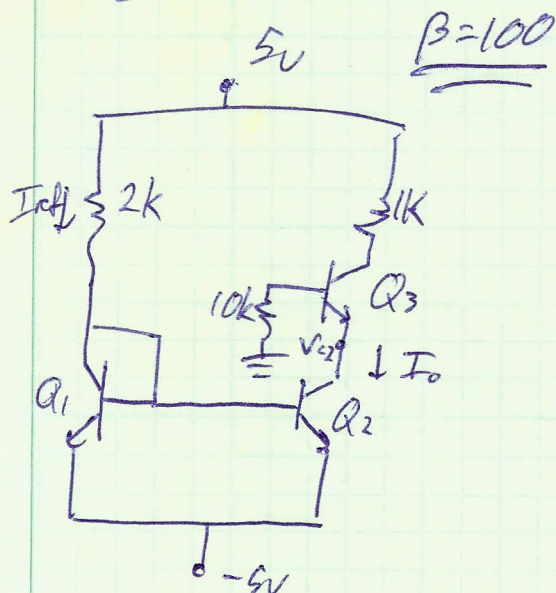
Current can be set with simple resistor



$$V_{CC} = I_{ref} R_C + V_{BE1} - V_{EE}$$

$$I_{ref} = \frac{V_{CC} + V_{EE} - V_{BE1}}{R_C} = \text{constant}$$

Example



$$BE1-KVL: 5 = 2k I_{ref} + V_{BE1} - 5$$

$$I_{ref} = 4.65 \text{ mA}$$

$$I_{E3} \approx I_O \approx 4.65 \text{ mA}$$

$$I_{B3} = \frac{I_{E3}}{1+\beta} = 46 \mu\text{A}$$

$$I_{C3} = I_{E3} - I_{B3} = 4.6 \text{ mA}$$

$$BE3-KVL: 0 = 10k \cdot I_{B3} + V_{BE3} + V_{C2}$$

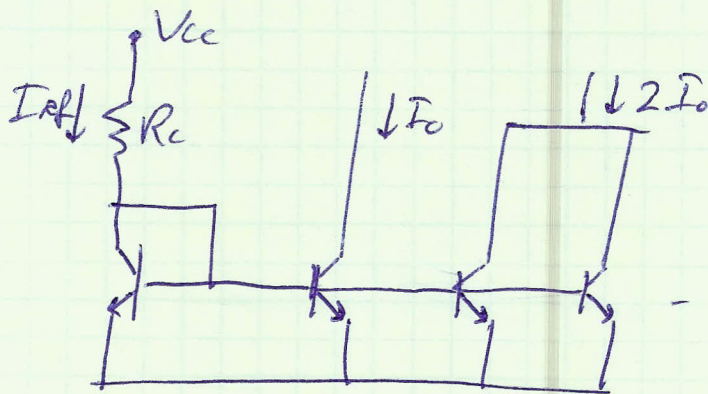
$$\rightarrow V_{C2} = -1.16 \text{ V}$$

$$Q_2 \text{ is active: } V_{CE2} = V_{C2} - (-5) = 3.84 \text{ V} > V_{DO}$$

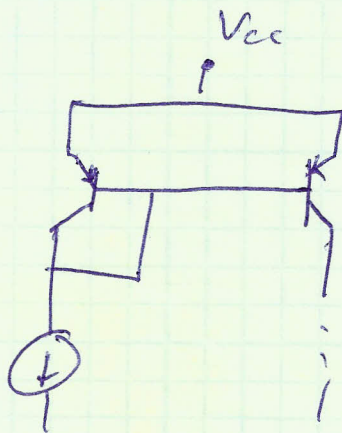
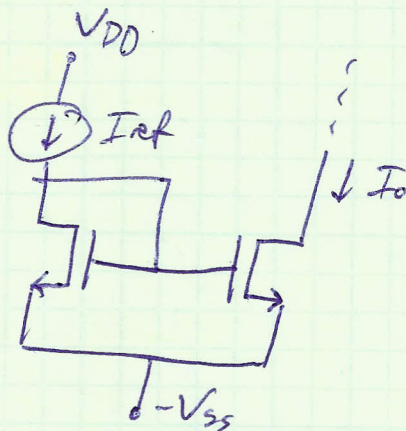
$$CE3-KVL: 5 = 1k \cdot I_{C3} + V_{CE3} + V_{C2}$$

$$\rightarrow V_{CE3} = 1.56 \text{ V} > V_{DO}$$

$$Q_3 \text{ is active}$$

Other current mirrorsmultiple outputs

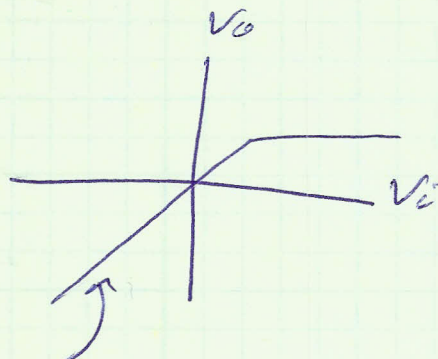
can also sum currents

PNP versionFET version

Small Signal Model

- Nonlinear devices behave as linear in small signal limit

Consider clipper circuit:



- circuit obviously behaves linearly here
- If we add 2 input voltages, we get sum at output
- Even in the clipped region if we add 2 input voltages, we will see something at the output

Example: $V_i = 5 + 0.05 \cos \omega t$

$\uparrow$ $\uparrow$
 bias signal

- With our piecewise linear model, $V_o = 0.7V$ always
- In reality, $V_o = 0.6921 + 0.0008 \cos \omega t$ (simulate it!)
- If we double the input signal, $V_i = 5 + 0.1 \cos \omega t$
 we get double the output signal: $V_o = 0.6921 + 0.0012 \cos \omega t$



The clipper circuit behaves linearly for small signals

- Sine wave in $\rightarrow$ Sine wave out
- proportional to input (double input $\rightarrow$ double output)
- we could also add other frequency components
- this is why we can build linear amplifiers with nonlinear devices
- devices must always be in one state, e.g. ON, active, etc.
- note that any nonlinear function can be approximated by its tangent line for values close to a given point

We can see this from the Taylor series expansion:

$$f(x_0 + \Delta x) = f(x_0) + \Delta x \frac{df}{dx} \bigg|_{x=x_0} + \frac{(\Delta x)^2}{2!} \frac{d^2 f}{dx^2} \bigg|_{x=x_0} + \dots$$

If Δx is small, $(\Delta x)^n$ is small for $n=2, 3, \dots$

Diode small signal model

$$I_D(V_D + v_d) \approx I_D(V_D) + v_d \frac{dI_D}{dV_D} \bigg|_{V_D=V_D}$$

$$= I_D + v_d \frac{dI_D}{dV_D} \bigg|_{V_D=V_D}$$

$\uparrow$
bias current

$\nwarrow$ response to signal



Diode response to small signal is like a resistor

$$i_d = v_d / r_d$$

$$r_d \equiv \left(di_d / dv_d |_{v_d = v_D} \right)^{-1}$$

r_d is inverse of slope of tangent line at bias point

find r_d from full expression for diode current:

$$i_D = I_s e^{v_D / nV_T}$$

$$\frac{di_D}{dv_D} = \frac{1}{nV_T} \times I_s e^{v_D / nV_T}$$

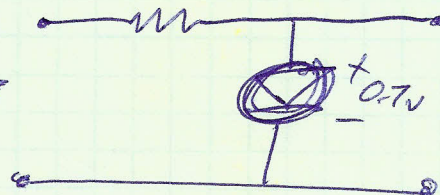
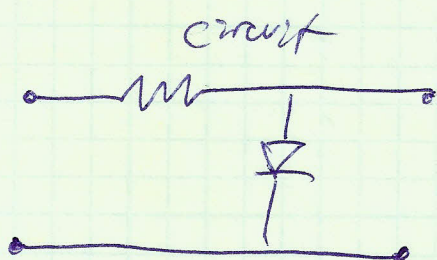
$$\left. \frac{di_D}{dv_D} \right|_{v_D = v_D} = \frac{1}{nV_T} I_s e^{v_D / nV_T} = \frac{I_D}{nV_T}$$

$$r_d = \frac{nV_T}{I_D}$$

$\nwarrow$ I_D is the bias current

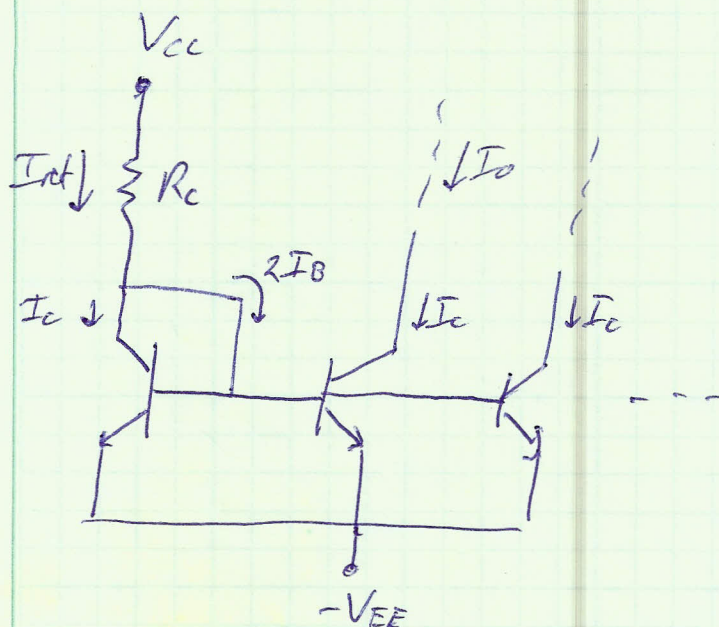
r_d changes with temperature through V_T

bias analysis (large sig.)



small signal analysis



Current MirrorsSummary

for single current mirror

$$\frac{I_O}{I_{ref}} = \frac{\beta}{\beta + 2}$$

I_O can be multiplied by using multiple transistors at output

- MOSFET current mirror is similar but we can scale W/L instead of using multiple transistors

Diode Small Signal Model

In on state:

$$\text{Diode} \rightarrow r_d = \frac{nV_T}{I_D}$$

I_D is DC bias current

$n = 2$ for discrete silicon diodes

$V_T = 25 \text{ mV}$ at 300 K